# 2SB1414

## Silicon PNP epitaxial planar type

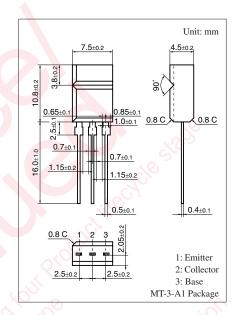
For low-frequency driver/high power amplification Complementary to 2SD2134

#### ■ Features

- ullet Excellent current  $I_C$  characteristics of forward current transfer ratio  $h_{FE}$  vs. collector
- High transition frequency f<sub>T</sub>
- Allowing automatic insertion with radial taping

## ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter                             | Symbol           | Rating      | Unit |  |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | $V_{CBO}$        | -150        | V    |  |
| Collector-emitter voltage (Base open) | V <sub>CEO</sub> | -150        | V    |  |
| Emitter-base voltage (Collector open) | $V_{EBO}$        | -5          | V    |  |
| Collector current                     | $I_{C}$          | -1          | A    |  |
| Peak collector current                | $I_{CP}$         | -1.5        | A    |  |
| Collector power dissipation           | P <sub>C</sub>   | 1.5         | W    |  |
| Junction temperature                  | Tj               | 150         | °CO  |  |
| Storage temperature                   | T <sub>stg</sub> | -55 to +150 | °C   |  |



## ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter                               | Symbol               | Conditions   | Min  | Тур   | Max  | Unit |
|---|----------------------|--|------|-------|------|------|
| Collector-emitter voltage (Base open)   | $V_{CEO}$            | $I_C = -100 \mu\text{A},  I_B = 0$                                 | -150 |       |      | V    |
| Emiter-base voltage (Collector open)    | $V_{EBO}$            | $I_E = -10 \mu\text{A},  I_C = 0$                                  | -5   |       |      | V    |
| Forward current transfer ratio *1       | h <sub>FE1</sub> *2  | $V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$                  | 90   |       | 330  | _    |
|   | h <sub>FE2</sub>     | $V_{CE} = -5 \text{ V}, I_C = -500 \text{ mA}$                     | 50   |       |      |      |
| Collector-emitter saturation voltage *1 | V <sub>CE(sat)</sub> | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$                      |      | - 0.5 | -2.0 | V    |
| Base-emitter saturation voltage *1      | V <sub>BE(sat)</sub> | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$                      |      | -1.0  | -2.0 | V    |
| Transition frequency                    | $f_T$                | $V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$ |      | 200   |      | MHz  |
| Collector output capacitance            | C <sub>ob</sub>      | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$               |      | 30    |      | pF   |
| (Common base, input open circuited)     |                      | VO. KI   |      |       |      |      |

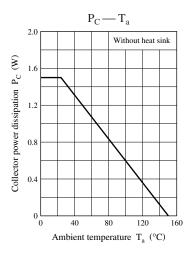
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

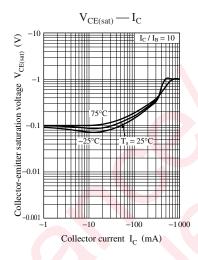
2. \*1: Pulse measurement

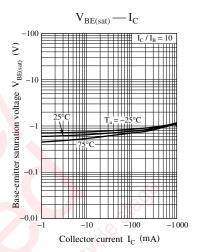
\*2: Rank classification

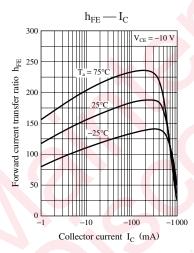
| Rank             | Q         | R          | S          |
|------------------|-----------|------------|------------|
| h <sub>FE1</sub> | 90 to 155 | 130 to 220 | 185 to 330 |

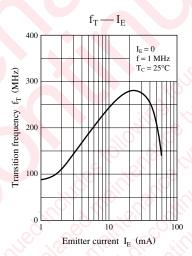
## **Panasonic**

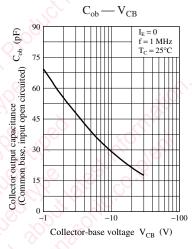


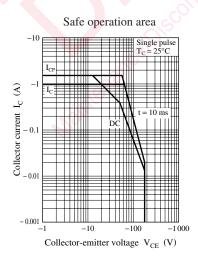


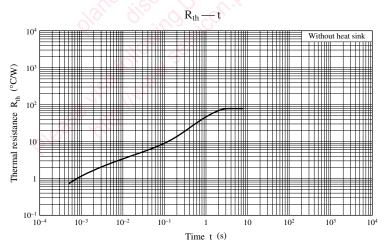












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